Characterization Table

S. No	W/L (PMOS)	W/L (NMOS)	Vth (V)	Id (A)	P (W)	tpd (ps)	Av	f (Hz)
1	2	1	2.776577e-01	63.9 uA	6.152262e-06	2.575706e-11	7.8565180	2.172236e+10
2	2	2	2.504164e-01	94 uA	8.664806e-06	2.539243e-11	7.944395	2.228675e+10
3	2	3	2.346182e-01	114 uA	1.039682e-05	2.520149e-11	8.051176	2.246232e+10
4	1	2	2.236636e-01	64 uA	5.902617e-06	2.507151e-11	8.148978	2.253315e+10
5	3	2	2.663854e-01	113.6 uA	1.069523e-05	2.557335e-11	7.878989e	2.196827e+10

- When Pfet width (no of fins increaded) increases the VTC Curve shifts towards right side.

- When Nfet width (Nfin) increases the VTC curve shifts left side.

- When width of any device nfet or pfet is increased then drain current will get increased also.

- When Nfet size increased then gain increases.

- Gain decreases when pfet size increases.

- Power is increased in both case.

- Drain current increases as drive strength increases.